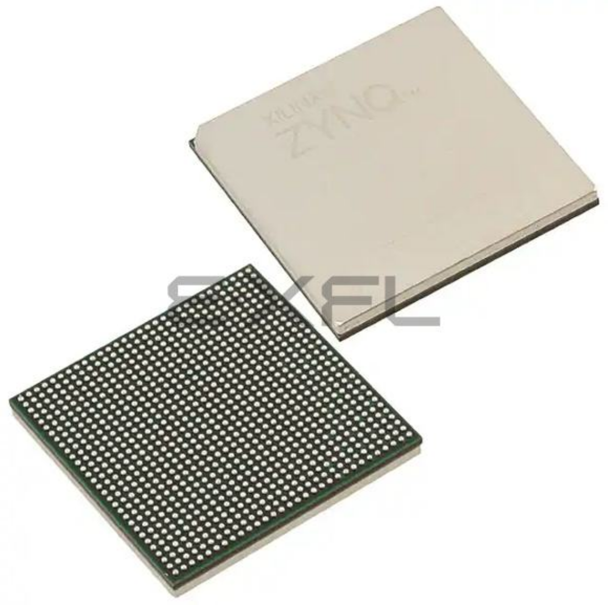
AMD Xilinx - XC7K410T-L2FFG900E Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	31775
Number of Logic Elements/Cells	406720
Total RAM Bits	29306880
Number of I/O	500
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k410t-l2ffg900e

Table 1: **Absolute Maximum Ratings (1)** ***(Cont'd)***

Symbol	Description	Min	Max	Units
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (6)	–	+260	°C
T_j	Maximum junction temperature(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC and AC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions (1)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}(2)	Internal supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCBRAM}(2)	Block RAM supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: block RAM supply voltage	0.87	0.90	1.03	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCO}(3)(4)	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
	Supply voltage for 1.8V HP I/O banks	1.14	–	1.89	V
V_{CCAUX_IO}	Auxiliary supply voltage when set to 1.8V	1.71	1.80	1.89	V
	Auxiliary supply voltage when set to 2.0V	1.94	2.00	2.06	V
V_{IN}(5)	I/O input voltage	–0.20	–	V_{CCO} + 0.2	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}(6)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(7)	Battery voltage	1.0	–	1.89	V
GTX Transceiver					
$V_{MGTAVCC}$(8)	Analog supply voltage for the GTX transceiver QPLL frequency range ≤ 10.3125 GHz(9)(10)	0.97	1.0	1.08	V
	Analog supply voltage for the GTX transceiver QPLL frequency range > 10.3125 GHz	1.02	1.05	1.08	V
$V_{MGTAVTT}$(8)	Analog supply voltage for the GTX transmitter and receiver termination circuits	1.17	1.2	1.23	V
$V_{MGTVCCAUX}$(8)	Auxiliary analog QPLL voltage supply for the transceivers	1.75	1.80	1.85	V

Table 2: **Recommended Operating Conditions** [(1)] ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$(8)	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}(2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}(3)	Battery supply current	–	–	150	nA

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks[1][2] *(Cont'd)***

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.80	9.71	–0.80	50.0
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7K70T	241	241	241	187	mA
		XC7K160T	474	474	474	368	mA
		XC7K325T	810	810	810	629	mA
		XC7K355T	993	993	993	771	mA
		XC7K410T	1080	1080	1080	838	mA
		XC7K420T	1313	1313	1313	1019	mA
		XC7K480T	1313	1313	1313	1019	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7K70T	1	1	1	1	mA
		XC7K160T	1	1	1	1	mA
		XC7K325T	1	1	1	1	mA
		XC7K355T	1	1	1	1	mA
		XC7K410T	1	1	1	1	mA
		XC7K420T	1	1	1	1	mA
		XC7K480T	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7K70T	21	21	21	21	mA
		XC7K160T	40	40	40	40	mA
		XC7K325T	68	68	68	68	mA
		XC7K355T	75	75	75	75	mA
		XC7K410T	85	85	85	85	mA
		XC7K420T	99	99	99	99	mA
		XC7K480T	99	99	99	99	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7K70T	N/A	N/A	N/A	N/A	mA
		XC7K160T	2	2	2	2	mA
		XC7K325T	2	2	2	2	mA
		XC7K355T	N/A	N/A	N/A	N/A	mA
		XC7K410T	2	2	2	2	mA
		XC7K420T	N/A	N/A	N/A	N/A	mA
		XC7K480T	N/A	N/A	N/A	N/A	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7K70T	6	6	6	6	mA
		XC7K160T	14	14	14	14	mA
		XC7K325T	19	19	19	19	mA
		XC7K355T	31	31	31	31	mA
		XC7K410T	34	34	34	34	mA
		XC7K420T	41	41	41	41	mA
		XC7K480T	41	41	41	41	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the XPower™ Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} – V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} – V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ}, that are required by Kintex-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Kintex-7 Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IOMIN}	$I_{CCBRAMMIN}$	Units
	Typ(1)	Typ(1)	Typ(1)	Typ(1)	Typ(1)	
XC7K70T	I_{CCINTQ} + 450	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K160T	I_{CCINTQ} + 550	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K325T	I_{CCINTQ} + 600	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K355T	I_{CCINTQ} + 1450	I_{CCAUXQ} + 109	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 81	mA
XC7K410T	I_{CCINTQ} + 1500	I_{CCAUXQ} + 125	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90	mA
XC7K420T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7K480T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the XPower Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100°C$(1)	–	500	ms
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in ISE® software 14.3 v1.07 for the -3, -2, -2L(1.0V), -1, and v1.06 for -2L(0.9V) speed grades.

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Kintex-7 FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 14 correlates the current status of each Kintex-7 device on a per speed grade basis.

Table 14: **Kintex-7 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7K70T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K160T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K325T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K355T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K410T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K420T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K480T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 15 lists the production released Kintex-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 15: **Kintex-7 Device Production Software and Speed Specification Release**

Device	Speed Grade Designations			
	1.0V			0.9V
	-3	-2/-2L	-1	-2L
XC7K70T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K160T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K325T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K355T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K410T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K420T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K480T	ISE 14.2 v1.06			ISE 14.3 v1.06

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Kintex-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the AC Switching Characteristics, page 11. In each table, the I/O bank type is either High Performance (HP) or High Range (HR).

Table 16: **Networking Applications Interface Performances**

Description	I/O Bank Type	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s
SDR LVDS receiver (SFI-4.1)(1)	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS receiver (SPI-4.2)(1)	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 17: **Maximum Physical Interface (PHY) Rate for Memory Interfaces (FFG Packages)(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	2.0V	1866	1866	1600	1333	Mb/s
	HP	1.8V	1600	1333	1066	1066	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1600	1600	1333	1066	Mb/s
	HP	1.8V	1333	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	800	800	800	Mb/s
RLDRAM III(3)	HP	2.0V	800	667	667	533	MHz
	HP	1.8V	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V					
	HR	N/A					
QDR II+(4)	HP	2.0V	550	500	450	450	MHz
	HP	1.8V					
	HR	N/A	500	450	400	400	MHz
RLDRAM II	HP	2.0V	533	500	450	450	MHz
	HP	1.8V					
	HR	N/A					
LPDDR2(3)	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
4. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

Table 18: **Maximum Physical Interface (PHY) Rate for Memory Interfaces (FBG Packages)(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}(3)	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	N/A	1333	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
RLDRAM III(4)	HP	N/A	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	N/A	1066	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
QDR II+(5)	HP	N/A	550	500	450	450	MHz
	HR	N/A	450	400	350	350	MHz
RLDRAM II	HP	N/A	533	500	450	450	MHz
	HR	N/A					
LPDDR2(4)	HP	N/A	667	667	667	667	Mb/s
	HR	N/A	667	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. FBG packages do not have separate V_{CCAUX_IO} supply pins to adjust the pre-driver voltage of the HP I/O banks.
4. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
5. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.31	1.42	1.64	1.51	5.27	5.63	6.05	4.13	6.03	6.49	7.04	4.64	ns
LVTTL_S8	1.31	1.42	1.64	1.51	4.45	4.83	5.30	3.86	5.21	5.69	6.29	4.38	ns
LVTTL_S12	1.31	1.42	1.64	1.51	4.45	4.83	5.29	3.84	5.21	5.69	6.28	4.36	ns
LVTTL_S16	1.31	1.42	1.64	1.51	3.47	3.88	4.40	3.39	4.23	4.74	5.39	3.91	ns
LVTTL_S24	1.31	1.42	1.64	1.51	3.58	3.99	4.51	3.61	4.34	4.85	5.50	4.13	ns
LVTTL_F4	1.31	1.42	1.64	1.51	4.70	4.98	5.29	3.58	5.46	5.84	6.28	4.09	ns
LVTTL_F8	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.06	4.42	4.92	5.55	3.58	ns
LVTTL_F12	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.05	4.42	4.92	5.55	3.56	ns
LVTTL_F16	1.31	1.42	1.64	1.51	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVTTL_F24	1.31	1.42	1.64	1.51	2.41	2.64	2.89	2.94	3.17	3.50	3.88	3.45	ns
LVDS_25(1)	0.64	0.68	0.80	0.83	1.36	1.47	1.55	1.58	2.12	2.33	2.54	2.09	ns
MINI_LVDS_25	0.68	0.70	0.79	0.83	1.36	1.47	1.55	1.59	2.12	2.33	2.54	2.11	ns
BLVDS_25(1)	0.65	0.69	0.80	0.83	1.83	2.02	2.20	2.16	2.59	2.88	3.19	2.67	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	0.83	1.36	1.48	1.55	1.59	2.12	2.34	2.54	2.11	ns
PPDS_25(1)	0.65	0.69	0.80	0.83	1.36	1.49	1.58	1.59	2.12	2.35	2.57	2.11	ns
TMDS_33(1)	0.72	0.76	0.86	0.83	1.43	1.54	1.60	1.70	2.19	2.40	2.59	2.22	ns
PCI33_3(1)	1.28	1.41	1.65	1.50	2.71	3.08	3.52	3.42	3.47	3.94	4.51	3.94	ns
HSUL_12	0.63	0.64	0.71	0.79	2.06	2.31	2.59	2.13	2.82	3.17	3.58	2.64	ns
DIFF_HSUL_12	0.58	0.61	0.70	0.81	1.83	2.04	2.26	1.92	2.59	2.90	3.25	2.44	ns
HSTL_I_S	0.61	0.64	0.73	0.79	1.55	1.69	1.80	1.91	2.31	2.55	2.79	2.42	ns
HSTL_II_S	0.61	0.64	0.73	0.78	1.21	1.34	1.43	1.70	1.97	2.20	2.42	2.22	ns
HSTL_I_18_S	0.64	0.67	0.76	0.79	1.28	1.39	1.45	1.58	2.04	2.25	2.44	2.09	ns
HSTL_II_18_S	0.64	0.67	0.76	0.79	1.18	1.31	1.40	1.69	1.94	2.17	2.39	2.20	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	0.78	1.42	1.54	1.61	1.84	2.18	2.40	2.60	2.36	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	0.79	1.15	1.24	1.27	1.78	1.91	2.10	2.26	2.30	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	0.79	1.27	1.38	1.43	1.67	2.03	2.24	2.42	2.19	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	0.81	1.14	1.23	1.26	1.72	1.90	2.09	2.25	2.23	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
HSTL_I_F	0.61	0.64	0.73	0.79	1.10	1.19	1.23	1.41	1.86	2.05	2.22	1.92	ns
HSTL_II_F	0.61	0.64	0.73	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
HSTL_I_18_F	0.64	0.67	0.76	0.79	1.05	1.18	1.28	1.44	1.81	2.04	2.27	1.95	ns
HSTL_II_18_F	0.64	0.67	0.76	0.79	1.03	1.14	1.23	1.42	1.79	2.00	2.22	1.94	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	0.78	1.09	1.18	1.22	1.48	1.85	2.04	2.21	2.00	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	0.79	1.02	1.11	1.14	1.48	1.78	1.97	2.13	2.00	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	0.79	1.08	1.17	1.21	1.48	1.84	2.03	2.20	2.00	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	0.81	1.01	1.10	1.13	1.48	1.77	1.96	2.12	2.00	ns
LVCMOS33_S4	1.31	1.40	1.60	1.54	5.23	5.61	6.09	4.13	5.99	6.47	7.08	4.64	ns
LVCMOS33_S8	1.31	1.40	1.60	1.54	4.46	4.85	5.33	3.84	5.22	5.71	6.32	4.36	ns
LVCMOS33_S12	1.31	1.40	1.60	1.54	3.46	3.89	4.42	3.41	4.22	4.75	5.41	3.92	ns
LVCMOS33_S16	1.31	1.40	1.60	1.54	3.06	3.43	3.88	3.72	3.82	4.29	4.87	4.23	ns
LVCMOS33_F4	1.31	1.40	1.60	1.54	4.70	5.01	5.36	3.58	5.46	5.87	6.35	4.09	ns
LVCMOS33_F8	1.31	1.40	1.60	1.54	3.62	4.04	4.56	3.06	4.38	4.90	5.55	3.58	ns
LVCMOS33_F12	1.31	1.40	1.60	1.54	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVCMOS33_F16	1.31	1.40	1.60	1.54	2.44	2.69	2.96	2.88	3.20	3.55	3.95	3.39	ns
LVCMOS25_S4	1.08	1.16	1.32	1.36	4.49	4.80	5.16	3.44	5.25	5.66	6.15	3.95	ns
LVCMOS25_S8	1.08	1.16	1.32	1.36	3.66	4.04	4.49	3.20	4.42	4.90	5.48	3.72	ns
LVCMOS25_S12	1.08	1.16	1.32	1.36	2.77	3.10	3.49	2.80	3.53	3.96	4.48	3.31	ns
LVCMOS25_S16	1.08	1.16	1.32	1.36	3.24	3.62	4.09	3.14	4.00	4.48	5.08	3.66	ns
LVCMOS25_F4	1.08	1.16	1.32	1.36	3.96	4.31	4.72	3.06	4.72	5.17	5.71	3.58	ns
LVCMOS25_F8	1.08	1.16	1.32	1.36	2.43	2.87	3.42	2.50	3.19	3.73	4.41	3.02	ns
LVCMOS25_F12	1.08	1.16	1.32	1.36	2.23	2.63	3.13	2.48	2.99	3.49	4.12	3.00	ns
LVCMOS25_F16	1.08	1.16	1.32	1.36	1.92	2.17	2.45	2.33	2.68	3.03	3.44	2.84	ns
LVCMOS18_S4	0.64	0.66	0.74	0.87	3.24	3.45	3.66	1.91	4.00	4.31	4.65	2.42	ns
LVCMOS18_S8	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S12	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S16	0.64	0.66	0.74	0.87	1.82	2.03	2.24	1.84	2.58	2.89	3.23	2.36	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	0.87	1.74	1.92	2.08	1.92	2.50	2.78	3.07	2.44	ns
LVCMOS18_F4	0.64	0.66	0.74	0.87	3.12	3.31	3.49	1.77	3.88	4.17	4.48	2.28	ns
LVCMOS18_F8	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F12	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F16	0.64	0.66	0.74	0.87	1.52	1.68	1.81	1.72	2.28	2.54	2.80	2.23	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	0.87	1.34	1.46	1.55	1.66	2.10	2.32	2.54	2.17	ns
LVCMOS15_S4	0.66	0.69	0.81	0.90	3.48	3.74	4.03	2.22	4.24	4.60	5.02	2.73	ns
LVCMOS15_S8	0.66	0.69	0.81	0.90	2.37	2.67	3.01	2.41	3.13	3.53	4.00	2.92	ns
LVCMOS15_S12	0.66	0.69	0.81	0.90	1.83	2.03	2.23	1.91	2.59	2.89	3.22	2.42	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVCMOS15_S16	0.66	0.69	0.81	0.90	1.76	1.95	2.13	1.91	2.52	2.81	3.12	2.42	ns
LVCMOS15_F4	0.66	0.69	0.81	0.90	3.39	3.60	3.80	1.98	4.15	4.46	4.79	2.50	ns
LVCMOS15_F8	0.66	0.69	0.81	0.90	1.79	1.99	2.18	1.92	2.55	2.85	3.17	2.44	ns
LVCMOS15_F12	0.66	0.69	0.81	0.90	1.40	1.54	1.65	1.67	2.16	2.40	2.64	2.19	ns
LVCMOS15_F16	0.66	0.69	0.81	0.90	1.37	1.51	1.61	1.66	2.13	2.37	2.60	2.17	ns
LVCMOS12_S4	0.88	0.91	1.00	1.01	3.85	4.22	4.69	2.89	4.61	5.08	5.68	3.41	ns
LVCMOS12_S8	0.88	0.91	1.00	1.01	2.52	2.96	3.52	2.41	3.28	3.82	4.51	2.92	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.01	2.06	2.31	2.59	2.11	2.82	3.17	3.58	2.63	ns
LVCMOS12_F4	0.88	0.91	1.00	1.01	3.44	3.73	4.06	2.30	4.20	4.59	5.05	2.81	ns
LVCMOS12_F8	0.88	0.91	1.00	1.01	1.72	2.04	2.40	1.86	2.48	2.90	3.39	2.38	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.01	1.54	1.71	1.87	1.69	2.30	2.57	2.86	2.20	ns
SSTL135_S	0.61	0.64	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
SSTL15_S	0.61	0.64	0.73	0.73	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
SSTL18_I_S	0.64	0.67	0.76	0.79	1.59	1.74	1.85	1.95	2.35	2.60	2.84	2.47	ns
SSTL18_II_S	0.64	0.67	0.76	0.78	1.27	1.40	1.50	1.63	2.03	2.26	2.49	2.14	ns
DIFF_SSTL135_S	0.59	0.61	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
DIFF_SSTL15_S	0.63	0.67	0.77	0.79	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	0.79	1.50	1.63	1.72	1.95	2.26	2.49	2.71	2.47	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	0.79	1.13	1.22	1.25	1.66	1.89	2.08	2.24	2.17	ns
SSTL135_F	0.61	0.64	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
SSTL15_F	0.61	0.64	0.73	0.73	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
SSTL18_I_F	0.64	0.67	0.76	0.79	1.12	1.22	1.26	1.44	1.88	2.08	2.25	1.95	ns
SSTL18_II_F	0.64	0.67	0.76	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
DIFF_SSTL135_F	0.59	0.61	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
DIFF_SSTL15_F	0.63	0.67	0.77	0.79	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	0.79	1.10	1.19	1.23	1.52	1.86	2.05	2.22	2.03	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	0.79	1.02	1.10	1.14	1.50	1.78	1.96	2.13	2.02	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Input Serializer/Deserializer Switching Characteristics

Table 24: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin Setup/Hold with respect to CLKDIV	0.01/0.12	0.02/0.13	0.02/0.15	0.02/0.21	ns
T_{ISCCK_CE}/ T_{ISCKC_CE}[2]	CE pin Setup/Hold with respect to CLK (for CE1)	0.39/–0.02	0.44/–0.02	0.63/–0.02	0.51/–0.22	ns
T_{ISCCK_CE2}/ T_{ISCKC_CE2}[2]	CE pin Setup/Hold with respect to CLKDIV (for CE2)	–0.12/0.29	–0.12/0.31	–0.12/0.35	–0.17/0.40	ns
Setup/Hold for Data Lines						
T_{ISDCK_D}/T_{ISCKD_D}	D pin Setup/Hold with respect to CLK	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.04/0.19	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IDELAY)[1]	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.03/0.19	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode	–0.02/0.11	–0.02/0.12	–0.02/0.15	–0.04/0.19	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode (using IDELAY)[1]	0.11/0.11	0.12/0.12	0.15/0.15	0.19/0.19	ns
Sequential Delays						
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.46	0.47	0.58	0.67	ns
Propagation Delays						
T_{ISDO_DO}	D input to DO output pin	0.09	0.10	0.12	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Table 27: **IO_FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T_{OFFCKO_DO}	RDCLK to Q outputs	0.51	0.56	0.63	0.81	ns
T_{CKO_FLAGS}	Clock to IO_FIFO Flags	0.59	0.62	0.81	0.77	ns
Setup/Hold						
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK	0.43/–0.01	0.47/–0.01	0.53/–0.01	0.76/–0.05	ns
$T_{IFFCCK\_WREN}/T_{IFFCKC\_WREN}$	WREN to WRCLK	0.39/–0.01	0.43/–0.01	0.50/–0.01	0.70/–0.05	ns
$T_{OFFCCK\_RDEN}/T_{OFFCKC\_RDEN}$	RDEN to RDCLK	0.49/0.01	0.53/0.02	0.61/0.02	0.79/–0.02	ns
Minimum Pulse Width						
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
Maximum Frequency						
F_{MAX}	RDCLK and WRCLK	533.05	470.37	400.00	333.33	MHz

MMCM Switching Characteristics

Table 38: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
MMCM_F_{INMAX}	Maximum Input Clock Frequency	1066.00	933.00	800.00	800.00	MHz
MMCM_F_{INMIN}	Minimum Input Clock Frequency	10.00	10.00	10.00	10.00	MHz
MMCM_$F_{INJITTER}$	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
MMCM_F_{INDUTY}	Allowable Input Duty Cycle: 10—49 MHz	25.00	25.00	25.00	25.00	%
	Allowable Input Duty Cycle: 50—199 MHz	30.00	30.00	30.00	30.00	%
	Allowable Input Duty Cycle: 200—399 MHz	35.00	35.00	35.00	35.00	%
	Allowable Input Duty Cycle: 400—499 MHz	40.00	40.00	40.00	40.00	%
	Allowable Input Duty Cycle: >500 MHz	45.00	45.00	45.00	45.00	%
MMCM_F_{MIN_PSCLK}	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
MMCM_F_{MAX_PSCLK}	Maximum Dynamic Phase Shift Clock Frequency	550.00	500.00	450.00	450.00	MHz
MMCM_F_{VCOMIN}	Minimum MMCM VCO Frequency	600.00	600.00	600.00	600.00	MHz
MMCM_F_{VCOMAX}	Maximum MMCM VCO Frequency	1600.00	1440.00	1200.00	1200.00	MHz
MMCM_$F_{BANDWIDTH}$	Low MMCM Bandwidth at Typical(1)	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical(1)	4.00	4.00	4.00	4.00	MHz
MMCM_$T_{STATPHAOFFSET}$	Static Phase Offset of the MMCM Outputs(2)	0.12	0.12	0.12	0.12	ns
MMCM_$T_{OUTJITTER}$	MMCM Output Jitter	Note 3				
MMCM_$T_{OUTDUTY}$	MMCM Output Clock Duty Cycle Precision(4)	0.20	0.20	0.20	0.25	ns
MMCM_$T_{LOCKMAX}$	MMCM Maximum Lock Time	100.00	100.00	100.00	100.00	µs
MMCM_F_{OUTMAX}	MMCM Maximum Output Frequency	1066.00	933.00	800.00	800.00	MHz
MMCM_F_{OUTMIN}	MMCM Minimum Output Frequency(5)(6)	4.69	4.69	4.69	4.69	MHz
MMCM_$T_{EXTFDVAR}$	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				
MMCM_$RST_{MINPULSE}$	Minimum Reset Pulse Width	5.00	5.00	5.00	5.00	ns
MMCM_F_{PFDMAX}	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	550.00	500.00	450.00	450.00	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300.00	300.00	300.00	300.00	MHz
MMCM_F_{PFDMIN}	Minimum Frequency at the Phase Frequency Detector	10.00	10.00	10.00	10.00	MHz
MMCM_$T_{FBDELAY}$	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
MMCM Switching Characteristics Setup and Hold						
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and Hold of Phase Shift Enable	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and Hold of Phase Shift Increment/Decrement	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase Shift Clock-to-Out of PSDONE	0.59	0.68	0.81	0.78	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK						
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min

Table 38: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN Setup/Hold	1.76/0.00	1.97/0.00	2.29/0.00	2.40/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY	0.65	0.72	0.99	0.70	ns, Max
F_{DCK}	DCLK frequency	200.00	200.00	200.00	100.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
   See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, MMCM_F_{OUTMIN} is 0.036 MHz.

PLL Switching Characteristics

Table 39: **PLL Specification**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
PLL_F_{INMAX}	Maximum Input Clock Frequency	1066.00	933.00	800.00	800.00	MHz
PLL_F_{INMIN}	Minimum Input Clock Frequency	19.00	19.00	19.00	19.00	MHz
PLL_$F_{INJITTER}$	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
PLL_F_{INDUTY}	Allowable Input Duty Cycle: 19—49 MHz	25.00	25.00	25.00	25.00	%
	Allowable Input Duty Cycle: 50—199 MHz	30.00	30.00	30.00	30.00	%
	Allowable Input Duty Cycle: 200—399 MHz	35.00	35.00	35.00	35.00	%
	Allowable Input Duty Cycle: 400—499 MHz	40.00	40.00	40.00	40.00	%
	Allowable Input Duty Cycle: >500 MHz	45.00	45.00	45.00	45.00	%
PLL_F_{VCOMIN}	Minimum PLL VCO Frequency	800.00	800.00	800.00	800.00	MHz
PLL_F_{VCOMAX}	Maximum PLL VCO Frequency	2133.00	1866.00	1600.00	1600.00	MHz
PLL_$F_{BANDWIDTH}$	Low PLL Bandwidth at Typical(1)	1.00	1.00	1.00	1.00	MHz
	High PLL Bandwidth at Typical(1)	4.00	4.00	4.00	4.00	MHz
PLL_$T_{STATPHAOFFSET}$	Static Phase Offset of the PLL Outputs(2)	0.12	0.12	0.12	0.12	ns
PLL_$T_{OUTJITTER}$	PLL Output Jitter	Note 3				
PLL_$T_{OUTDUTY}$	PLL Output Clock Duty Cycle Precision(4)	0.20	0.20	0.20	0.25	ns
PLL_$T_{LOCKMAX}$	PLL Maximum Lock Time	100	100	100	100	µs
PLL_F_{OUTMAX}	PLL Maximum Output Frequency	1066.00	933.00	800.00	800.00	MHz
PLL_F_{OUTMIN}	PLL Minimum Output Frequency(5)	6.25	6.25	6.25	6.25	MHz
PLL_$T_{EXTFDVAR}$	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				
PLL_$RST_{MINPULSE}$	Minimum Reset Pulse Width	5.00	5.00	5.00	5.00	ns

Table 52 summarizes the DC specifications of the clock input of the GTX transceiver. Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further details.

Table 52: **GTX Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	100	–	nF

GTX Transceiver Switching Characteristics

Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further information.

Table 53: **GTX Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1[1]		-2L[2]		
			Package Type								
			FF	FB	FF	FB	FF	FB	FF	FB	
F_{GTXMAX}[3]	Maximum GTX transceiver data rate		12.5	6.6	10.3125	6.6	8.0	6.6	6.6	6.6	Gb/s
F_{GTXMIN}[3]	Minimum GTX transceiver data rate		0.500	0.500	0.500	0.500	0.500	0.500	0.500	0.500	Gb/s
$F_{GTXCRANGE}$	CPLL line rate range	1	3.2–6.6								Gb/s
		2	1.6–3.3								Gb/s
		4	0.8–1.65								Gb/s
		8	0.5–0.825								Gb/s
		16	N/A								Gb/s
$F_{GTXQRANGE1}$	QPLL line rate range 1	1	5.93–8.0	5.93–6.6	5.93–8.0	5.93–6.6	5.93–8.0	5.93–6.6	5.93–6.6		Gb/s
		2	2.965–4.0		2.965–4.0		2.965–4.0		2.965–3.3		Gb/s
		4	1.4825–2.0		1.4825–2.0		1.4825–2.0		1.4825–1.65		Gb/s
		8	0.74125–1.0		0.74125–1.0		0.74125–1.0		0.74125–0.825		Gb/s
		16	N/A		N/A		N/A		N/A		Gb/s
$F_{GTXQRANGE2}$	QPLL line rate range 2[4]	1	9.8–12.5	N/A	9.8–10.3125	N/A	N/A		N/A		Gb/s
		2	4.9–6.25		4.9–5.15625		N/A		N/A		Gb/s
		4	2.45–3.125		2.45–2.578125		N/A		N/A		Gb/s
		8	1.225–1.5625		1.225–1.2890625		N/A		N/A		Gb/s
		16	0.6125–0.78125		0.6125–0.64453125		N/A		N/A		Gb/s
$F_{GCPLLRANGE}$	GTX transceiver CPLL frequency range		1.6–3.3		1.6–3.3		1.6–3.3		1.6–3.3		GHz
$F_{GQPLLRANGE1}$	GTX transceiver QPLL frequency range 1		5.93–8.0		5.93–8.0		5.93–8.0		5.93–6.6		GHz

Table 63: CEI-6G and CEI-11G Protocol Characteristics

Description	Line Rate (Mb/s)	Interface	Min	Max	Units
CEI-6G Transmitter Jitter Generation					
Total transmitter jitter[1]	4976–6375	CEI-6G-SR	–	0.3	UI
		CEI-6G-LR	–	0.3	UI
CEI-6G Receiver High Frequency Jitter Tolerance					
Total receiver jitter tolerance[1]	4976–6375	CEI-6G-SR	0.6	–	UI
		CEI-6G-LR	0.95	–	UI
CEI-11G Transmitter Jitter Generation					
Total transmitter jitter[2]	9950–11100	CEI-11G-SR	–	0.3	UI
		CEI-11G-LR/MR	–	0.3	UI
CEI-11G Receiver High Frequency Jitter Tolerance					
Total receiver jitter tolerance[2]	9950–11100	CEI-11G-SR	0.65	–	UI
		CEI-11G-MR	0.65	–	UI
		CEI-11G-LR	0.825	–	UI

Notes:

1. Tested at most commonly used line rate of 6250 Mb/s using 390.625 MHz reference clock.
2. Tested at line rate of 9950 Mb/s using 155.46875 MHz reference clock and 11100 Mb/s using 173.4375 MHz reference clock.

Table 64: SFP+ Protocol Characteristics

Description	Line Rate (Mb/s)	Min	Max	Units
SFP+ Transmitter Jitter Generation				
Total transmitter jitter	9830.40[1]	–	0.28	UI
	9953.00			
	10312.50			
	10518.75			
	11100.00			
SFP+ Receiver Frequency Jitter Tolerance				
Total receiver jitter tolerance	9830.40[1]	0.7	–	UI
	9953.00			
	10312.50			
	10518.75			
	11100.00			

Notes:

1. Line rated used for CPRI over SFP+ applications.

Date	Version	Description
07/25/12	1.6	Updated the descriptions, changed V_{IN} and Note 2 and added Note 4 in Table 1. In Table 2, changed descriptions and notes, removed Note 7, changed GTX transceiver parameters and values and added Note 9. Updated parameters in Table 3. Added Table 4 and Table 5. Changed the typical values for many of the devices in Table 7. Updated LVCMOS12 and the SSTLs in Table 9. Updated many of the specifications in Table 10 and Table 11. Updated speed specification to v1.06 (-3, -2, -2L(1.0V), -1) and v1.05 (-2L(0.9V)) with appropriate changes to Table 14 and Table 15 including production release of the XC7K325T and the XC7K410T in the -2, -2L(1.0V), and -1 speed designations. Added notes and specifications to Table 17 and Table 18. Updated the IOB Pad Input/Output/3-State discussion and changed Table 21 by adding $T_{IOIBUFDISABLE}$. Removed many of the combinatorial delay specifications and T_{CINCK}/T_{CKCIN} from Table 28. Rearranged Table 51 including moving some parameters to Table 1. Added Table 56. Updated Table 57. In Table 59, updated SJ Jitter Tolerance with Stressed Eye section, page 51 and Note 8. Added Note 1, Note 2, and Note 3 to Table 62. Added Note 1 and Note 2 to Table 63, and line rate ranges. Updated Table 64 including adding Note 1. Updated Table 65 including adding Note 1. In Table 67 updated Note 1 and added Note 4. In Table 68, updated T_{POR} and F_{EMCCK}.
09/04/12	1.7	Updated Table 14 and Table 15 for production release of the XC7K160T in the -2, -2L(1.0V), and -1 speed designations.
09/26/12	1.8	In Table 2, revised V_{CCINT} and V_{CCBRAM} and added Note 2. Updated Table 14 and Table 15 for production release of the XC7K480T in the -2, -2L(1.0V), and -1 speed designations and the XC7K325T and XC7K410T in the -3 speed designation.
10/10/12	1.9	Updated the $I_{CCINTMIN}$ value for the XC7K355T in Table 7. Updated Table 14 and Table 15 for production release of the XC7K420T in the -2, -2L(1.0V), and -1 speed designations.
10/25/12	2.0	Updated the AC Switching Characteristics based upon ISE 14.3 v1.07 for the -3, -2, -2L (1.0V), -1 speed specifications, and ISE 14.3 v1.06 for the -2L (0.9V) speed specifications throughout the document. Updated Table 14 and Table 15 for production release of the XC7K355T in the -2, -2L(1.0V), and -1 speed designations. Also updated Table 14 and Table 15 for production release of the XC7K325T and XC7K410T in the -2L (0.9V). Added values for Table 16 -2L (0.9V). Added package skew values to Table 50. In Table 53, increased -1 speed grade (FF package) F_{GTXMAX} value from 6.6 Gb/s to 8.0 Gb/s.
10/31/12	2.1	Updated Table 14 and Table 15 for production release of the XC7K70T in the -2, -2L(1.0V), and -1 speed designations.
11/26/12	2.2	Updated Table 14 and Table 15 for production release of -3 speed designation for XC7K70T, XC7K160T, XC7K355T, XC7K420T, and XC7K480T. Removed Note 4 from Table 67.
12/05/12	2.3	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K160T, XC7K420T, and XC7K480T. Updated Note 1 in Table 50.
12/12/12	2.4	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K70T and XC7K355T. Added Internal Configuration Access Port section to Table 68.